

David J Smith

List of Publications by Year in descending order

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675
papers

21,816
citations

12597

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25983

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docs citations

685
times ranked

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#	ARTICLE	IF	CITATIONS
1	Compositional Control and Optimization of Molecular Beam Epitaxial Growth of $(\text{Sb}_{2-x}\text{Te}_{3-x})_{1-x}(\text{MnSb}_{2-x}\text{Te}_{4-x})_x$ Magnetic Topological Insulators. <i>Crystal Growth and Design</i> , 2022, 22, 3007-3015.		6
2	The sound of recovery: Coral reef restoration success is detectable in the soundscape. <i>Journal of Applied Ecology</i> , 2022, 59, 742-756.	1.9	25
3	Keeping it Green. <i>ChemSusChem</i> , 2022, 15, e202102612.	3.6	0
4	A roadmap to integrating resilience into the practice of coral reef restoration. <i>Global Change Biology</i> , 2022, 28, 4751-4764.	4.2	27
5	Suppressed recovery of functionally important branching <i>Acropora</i> drives coral community composition changes following mass bleaching in Indonesia. <i>Coral Reefs</i> , 2022, 41, 1337-1350.	0.9	1
6	Impact of Individual Structural Defects in GaAs Solar Cells: A Correlative and In Operando Investigation of Signatures, Structures, and Effects. <i>Advanced Optical Materials</i> , 2021, 9, 2001487.	3.6	7
7	A Fresh Look at Sustainable Chemistry. <i>ChemSusChem</i> , 2021, 14, 5-9.	3.6	1
8	Knocking on the door: policy, agency and path creation in the post-industrial city. <i>European Planning Studies</i> , 2021, 29, 899-922.	1.6	0
9	Resolving conservation and development tensions in a small island state: A governance analysis of Curieuse Marine National Park, Seychelles. <i>Marine Policy</i> , 2021, 127, 103617.	1.5	7
10	Heads and Tails: Requirements for Informative and Robust Computational Measures of Sperm Motility. , 2021, , 135-150.		0
11	Atomic-Resolution Structure Imaging of Misfit Dislocations at Heterovalent II-VI/III-V Interfaces. <i>ACS Applied Electronic Materials</i> , 2021, 3, 2573-2579.	2.0	3
12	The Role of the Double-Layer Potential in Regularised Stokeslet Models of Self-Propulsion. <i>Fluids</i> , 2021, 6, 411.	0.8	1
13	Coral bleaching patterns are the outcome of complex biological and environmental networking. <i>Global Change Biology</i> , 2020, 26, 68-79.	4.2	111
14	Strategies for Analyzing Noncommon Atom Heterovalent Interfaces: The Case of CdTe/InSb . <i>Advanced Materials Interfaces</i> , 2020, 7, 1901658.	1.9	11
15	Structural breakdown in high power GaN-on-GaN p-n diode devices stressed to failure. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, 063402.	0.9	5
16	Atomic-resolution structure imaging of defects and interfaces in compound semiconductors. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2020, 66, 100498.	1.8	16
17	Dielectric breakdown in epitaxial BaTiO_3 thin films. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020, 38, 044007.	0.6	3
18	Formation of metastable bc8 phase from crystalline $\text{Si}_{0.5}\text{Ge}_{0.5}$ by high-pressure torsion. <i>Materials Characterization</i> , 2020, 169, 110590.	1.9	10

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19	Passively parallel regularized stokeslets. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2020, 378, 20190528.	1.6	6
20	Plasma Enhanced Atomic Layer-etched and Regrown GaN-on-GaN High Power <i>p-n</i> Diodes. Microscopy and Microanalysis, 2020, 26, 840-842.	0.2	1
21	Approaches to Phase Imaging in the Electron Microscope. Microscopy and Microanalysis, 2020, 26, 1546-1546.	0.2	0
22	A hyperspectral unmixing framework for energy-loss near-edge structure analysis. Ultramicroscopy, 2020, 218, 113096.	0.8	2
23	Effects of growth temperature on electrical properties of GaN/AlN based resonant tunneling diodes with peak current density up to 1.01 MA/cm ² . AIP Advances, 2020, 10, .	0.6	7
24	Annealing Effects on the Band Alignment of ALD SiO ₂ on (In _x Ga _{1-x}) ₂ O ₃ for x = 0.25~0.74. ECS Journal of Solid State Science and Technology, 2020, 9, 045001.	0.9	0
25	Direct Observation of Large Atomic Polar Displacements in Epitaxial Barium Titanate Thin Films. Advanced Materials Interfaces, 2020, 7, 2000555.	1.9	8
26	Prevention of Adrenal Crisis: Cortisol Responses to Major Stress Compared to Stress Dose Hydrocortisone Delivery. Journal of Clinical Endocrinology and Metabolism, 2020, 105, 2262-2274.	1.8	68
27	Changes in band alignment during annealing at 600~°C of ALD Al ₂ O ₃ on (In _x Ga _{1-x}) ₂ O ₃ for x = 0.25~0.74. Journal of Applied Physics, 2020, 127, 105701.	1.1	6
28	Lucky Thirteen. ChemSusChem, 2020, 13, 6-10.	3.6	0
29	Investigation of polycrystalline Ga _x In _{1-x} P for potential use as a solar cell absorber with tunable bandgap. Journal of Applied Physics, 2020, 127, 073102.	1.1	3
30	Reverse Leakage Analysis for As-Grown and Regrown Vertical GaN-on-GaN Schottky Barrier Diodes. IEEE Journal of the Electron Devices Society, 2020, 8, 74-83.	1.2	42
31	Coral microbiome composition along the northern Red Sea suggests high plasticity of bacterial and specificity of endosymbiotic dinoflagellate communities. Microbiome, 2020, 8, 8.	4.9	75
32	Layered two-dimensional selenides and tellurides grown by molecular beam epitaxy. , 2020, , 235-269.		1
33	Rapid optofluidic detection of biomarkers for traumatic brain injury via surface-enhanced Raman spectroscopy. Nature Biomedical Engineering, 2020, 4, 610-623.	11.6	87
34	Doing more with less: The flagellar end piece enhances the propulsive effectiveness of human spermatozoa. Physical Review Fluids, 2020, 5, .	1.0	14
35	The Making of Innovative Entrepreneurs in Business Schools in a Resource Constrained Environment. Proceedings - Academy of Management, 2020, 2020, 19277.	0.0	0
36	Molecular beam epitaxial growth and structural properties of hetero-crystalline and heterovalent PbTe/CdTe/InSb structures. Journal of Applied Physics, 2019, 126, .	1.1	3

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37	Motile curved bacteria are Pareto-optimal. Proceedings of the National Academy of Sciences of the United States of America, 2019, 116, 14440-14447.	3.3	49
38	Growth Habits of Bismuth Selenide (Bi_2Se_3) Layers and Nanowires over Stranski-Krastanov Indium Arsenide Quantum Dots. Crystal Growth and Design, 2019, 19, 6989-6993.	1.4	3
39	Coral microbiome diversity reflects mass coral bleaching susceptibility during the 2016 El Niño heat wave. Ecology and Evolution, 2019, 9, 938-956.	0.8	81
40	Switching Behavior and Forward Bias Degradation of 700V, 0.2A, $\text{In}_2\text{Ga}_2\text{O}_3$ Vertical Geometry Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, Q3028-Q3033.	0.9	18
41	Defects at the surface of $\text{In}_2\text{Ga}_2\text{O}_3$ produced by Ar plasma exposure. APL Materials, 2019, 7, .	2.2	36
42	Damage Recovery and Dopant Diffusion in Si and Sn Ion Implanted $\text{In}_2\text{Ga}_2\text{O}_3$. ECS Journal of Solid State Science and Technology, 2019, 8, Q3133-Q3139.	0.9	29
43	Sharp Quadrature Error Bounds for the Nearest-Neighbor Discretization of the Regularized Stokeslet Boundary Integral Equation. SIAM Journal of Scientific Computing, 2019, 41, B139-B152.	1.3	8
44	Self-assembled Bismuth Selenide (Bi_2Se_3) quantum dots grown by molecular beam epitaxy. Scientific Reports, 2019, 9, 3370.	1.6	24
45	Strain-dependence of $\epsilon(2)$ in thin film barium strontium titanate. AIP Advances, 2019, 9, .	0.6	3
46	⁶⁰ Co Gamma Ray Damage in Homoepitaxial $\text{In}_2\text{Ga}_2\text{O}_3$ Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, Q3041-Q3045.	0.9	18
47	Quantitative measurement of nanoscale electrostatic potentials and charges using off-axis electron holography: Developments and opportunities. Ultramicroscopy, 2019, 203, 105-118.	0.8	22
48	<i>(Invited)</i> Comparison of High Voltage, Vertical Geometry Ga_2O_3 Rectifiers with GaN and SiC. ECS Transactions, 2019, 92, 15-24.	0.3	2
49	Epitaxial Oxides on Glass: A Platform for Integrated Oxide Devices. ACS Applied Nano Materials, 2019, 2, 7713-7718.	2.4	8
50	Microstructural Characterization of Defects and Chemical Etching for HgCdSe/ZnTe/Si (211) Heterostructures. Journal of Electronic Materials, 2019, 48, 571-582.	1.0	3
51	A Big Year for Chemistry and Sustainability. ChemSusChem, 2019, 12, 343-346.	3.6	0
52	Strain relaxation in low-mismatched GaAs/GaAs _{1-x} Sbx/GaAs heterostructures. Acta Materialia, 2019, 162, 103-115.	3.8	13
53	Electron Holography. Springer Handbooks, 2019, , 767-818.	0.3	16
54	DC and dynamic switching characteristics of field-plated vertical geometry $\text{In}_2\text{Ga}_2\text{O}_3$ rectifiers. , 2019, , .		2

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55	Surface structure analysis of Eu Zintl template on Ge(001). Surface Science, 2018, 674, 94-102.	0.8	9
56	BIOLOGICAL FLUID MECHANICS UNDER THE MICROSCOPE: A TRIBUTE TO JOHN BLAKE. ANZIAM Journal, 2018, 59, 416-442.	0.3	2
57	Green innovation and the development of sustainable communities. International Journal of Entrepreneurship and Innovation, 2018, 19, 21-32.	1.4	29
58	The Past, Present, and Future of Sustainable Chemistry. ChemSusChem, 2018, 11, 5-10.	3.6	7
59	Nottingham Express Transit. International Journal of Entrepreneurship and Innovation, 2018, 19, 56-68.	1.4	3
60	Growth of II-VI/III-V heterovalent quantum structures. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, .	0.6	10
61	Thermal refugia against coral bleaching throughout the northern Red Sea. Global Change Biology, 2018, 24, e474-e484.	4.2	177
62	Properties and Imaging of Thick Doped Amorphous Silicon in Direct Contact with Aluminum For Use in Silicon Heterojunction Solar Cells. , 2018, , .		0
63	Effect of SrTiO ₃ oxygen vacancies on the conductivity of LaTiO ₃ /SrTiO ₃ heterostructures. Journal of Applied Physics, 2018, 124, 185303.	1.1	22
64	EuO epitaxy by oxygen scavenging on SrTiO ₃ (001): Effect of SrTiO ₃ thickness and temperature. Journal of Applied Physics, 2018, 124, .	1.1	7
65	Investigation of defect creation in GaP/Si(O ⁻) epitaxial structures. Journal of Crystal Growth, 2018, 503, 36-44.	0.7	15
66	An EELS signal-from-background separation algorithm for spectral line-scan/image quantification. Ultramicroscopy, 2018, 195, 25-31.	0.8	6
67	Large positive linear magnetoresistance in the two-dimensional t _{2g} electron gas at the EuO/SrTiO ₃ interface. Scientific Reports, 2018, 8, 7721.	1.6	40
68	Nanoparticle transport across model cellular membranes: when do solubility-diffusion models break down?. Journal Physics D: Applied Physics, 2018, 51, 294004.	1.3	15
69	Crystalline SrZrO ₃ deposition on Ge (001) by atomic layer deposition for high- <i>k</i> dielectric applications. Journal of Applied Physics, 2018, 124, .	1.1	9
70	Atomic structure of dissociated 60Å ^o dislocations in GaAs/GaAs _{0.92} Sb _{0.08} /GaAs heterostructures. Scripta Materialia, 2018, 153, 77-80.	2.6	5
71	Impact of metastable phases on electrical properties of Si with different doping concentrations after processing by high-pressure torsion. Scripta Materialia, 2018, 157, 120-123.	2.6	12
72	Meshfree and efficient modeling of swimming cells. Physical Review Fluids, 2018, 3, .	1.0	21

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73	The scientific careers of Robert Sinclair and Nestor Zaluzec - A brief sketch. <i>Ultramicroscopy</i> , 2017, 176, 2-4.	0.8	0
74	Zintl layer formation during perovskite atomic layer deposition on Ge (001). <i>Journal of Chemical Physics</i> , 2017, 146, 052817.	1.2	11
75	Structural evolution of dilute magnetic (Sn,Mn)Se films grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2017, 121, 075301.	1.1	5
76	Unraveling Hydrophobic Interactions at the Molecular Scale Using Force Spectroscopy and Molecular Dynamics Simulations. <i>ACS Nano</i> , 2017, 11, 2586-2597.	7.3	37
77	Observation of compound semiconductors and heterovalent interfaces using aberration-corrected scanning transmission electron microscopy. <i>Journal of Materials Research</i> , 2017, 32, 921-927.	1.2	7
78	Surface preparation of freestanding GaN substrates for homoepitaxial GaN growth by rf-plasma MBE. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017, 35, .	0.6	24
79	High-resolution transmission electron microscopy analysis of bulk nanograined silicon processed by high-pressure torsion. <i>Materials Characterization</i> , 2017, 129, 163-168.	1.9	19
80	Correlation of Etch Pits and Dislocations in As-grown and Thermal Cycle-Annealed HgCdTe(211) Films. <i>Journal of Electronic Materials</i> , 2017, 46, 5007-5019.	1.0	7
81	Can Simple Interaction Models Explain Sequence-Dependent Effects in Peptide Homodimerization?. <i>Journal of Physical Chemistry B</i> , 2017, 121, 5928-5943.	1.2	2
82	Substrate-independent analysis of microcrystalline silicon thin films using UV Raman spectroscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1700204.	0.7	8
83	Recent studies of oxide-semiconductor heterostructures using aberration-corrected scanning transmission electron microscopy. <i>Journal of Materials Research</i> , 2017, 32, 912-920.	1.2	7
84	A Perfect Ten. <i>ChemSusChem</i> , 2017, 10, 2-5.	3.6	2
85	Band offsets of epitaxial cubic boron nitride deposited on polycrystalline diamond via plasma-enhanced chemical vapor deposition. <i>Applied Physics Letters</i> , 2017, 111, 171604.	1.5	20
86	Microscale magnetic compasses. <i>Journal of Applied Physics</i> , 2017, 122, .	1.1	0
87	High-resolution transmission electron microscopy analysis of nanograined germanium produced by high-pressure torsion. <i>Materials Characterization</i> , 2017, 132, 132-138.	1.9	23
88	Adaptive capability and path creation in the post-industrial city: the case of Nottingham's biotechnology sector. <i>Cambridge Journal of Regions, Economy and Society</i> , 2017, 10, 491-508.	1.7	8
89	Institutions, place leadership and public entrepreneurship: Reinterpreting the economic development of Nottingham. <i>Local Economy</i> , 2017, 32, 374-392.	0.8	20
90	Epitaxial growth of barium titanate thin films on germanium via atomic layer deposition. <i>Journal of Crystal Growth</i> , 2017, 476, 6-11.	0.7	13

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91	Integration of ferroelectric BaTiO ₃ with Ge: The role of a SrTiO ₃ buffer layer investigated using aberration-corrected STEM. Applied Physics Letters, 2017, 110, .	1.5	5
92	Above 400-K robust perpendicular ferromagnetic phase in a topological insulator. Science Advances, 2017, 3, e1700307.	4.7	138
93	AlGaIn/GaN High Electron Mobility Transistor Grown and Fabricated on ZrTi Metallic Alloy Buffer Layers. ECS Journal of Solid State Science and Technology, 2017, 6, S3078-S3080.	0.9	2
94	Characterization of electrical properties in axial Si-Ge nanowire heterojunctions using off-axis electron holography and atom-probe tomography. Journal of Applied Physics, 2016, 120, .	1.1	10
95	Monolithic integration of perovskites on Ge(001) by atomic layer deposition: a case study with SrHf _x Ti _{1-x} O ₃ . MRS Communications, 2016, 6, 125-132.	0.8	13
96	Bright-field imaging of compound semiconductors using aberration-corrected scanning transmission electron microscopy. Semiconductor Science and Technology, 2016, 31, 094002.	1.0	10
97	Structural characterization of niobium oxide thin films grown on SrTiO ₃ (111) and (La,Sr)(Al,Ta)O ₃ (111) substrates. Journal of Applied Physics, 2016, 120, 245302.	1.1	16
98	Evaluation of AlGaIn/GaN high electron mobility transistors grown on ZrTi buffer layers with sapphire substrates. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, 051208.	0.6	4
99	Continuous control of spin polarization using a magnetic field. Applied Physics Letters, 2016, 108, 212401.	1.5	1
100	Evaluation of antimony segregation in InAs/InAs _{1-x} Sb _x type-II superlattices grown by molecular beam epitaxy. Journal of Applied Physics, 2016, 119, .	1.1	45
101	Investigation of dilute-nitride alloys of GaAsN _x (0.01 ≤ x ≤ 0.04) grown by MBE on GaAs (001) substrates for photovoltaic solar cell devices. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, .	0.6	7
102	Anti-phase boundaries at the SrTiO ₃ /Si(001) interface studied using aberration-corrected scanning transmission electron microscopy. Applied Physics Letters, 2016, 108, .	1.5	16
103	Spectral identification scheme for epitaxially grown single-phase niobium dioxide. Journal of Applied Physics, 2016, 119, .	1.1	11
104	Morphological and microstructural stability of N-polar InAlN thin films grown on free-standing GaN substrates by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	0.9	4
105	Spectrum and phase mapping across the epitaxial $\hat{\Gamma}$ -Al ₂ O ₃ /SrTiO ₃ interface. Applied Physics Letters, 2016, 108, .	1.5	9
106	Effect of indium in Al _{0.65} Ga _{0.35} N/Al _{0.8} Ga _{0.2} N MQWs for the development of deep-UV laser structures in the form of graded-index separate confinement heterostructure (GRINSCH). Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1165-1169.	0.8	15
107	Impact of dynamical scattering on quantitative contrast for aberration-corrected transmission electron microscope images. Micron, 2016, 89, 77-86.	1.1	2
108	Critical issues for homoepitaxial GaN growth by molecular beam epitaxy on hydride vapor-phase epitaxy-grown GaN substrates. Journal of Crystal Growth, 2016, 456, 121-132.	0.7	28

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109	Characterization of structural defects in SnSe ₂ thin films grown by molecular beam epitaxy on GaAs (111)B substrates. Journal of Crystal Growth, 2016, 453, 58-64.	0.7	12
110	Impact of severe plastic deformation on microstructure and hydrogen storage of titanium-iron-manganese intermetallics. Scripta Materialia, 2016, 124, 108-111.	2.6	47
111	Contradictory nature of Co doping in ferroelectric BaTiO ₃ . Physical Review B, 2016, 94, .	1.1	8
112	Direct Mapping of Charge Distribution during Lithiation of Ge Nanowires Using Off-Axis Electron Holography. Nano Letters, 2016, 16, 3748-3753.	4.5	34
113	Towards defect-free epitaxial CdTe and MgCdTe layers grown on InSb (001) substrates. Journal of Crystal Growth, 2016, 439, 99-103.	0.7	12
114	Determination of Mean Inner Potential and Inelastic Mean Free Path of ZnTe Using Off-Axis Electron Holography and Dynamical Effects Affecting Phase Determination. Microscopy and Microanalysis, 2015, 21, 1406-1412.	0.2	9
115	Charge control in N-polar InAlN high-electron-mobility transistors grown by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, .	0.6	13
116	Effect of proton irradiation energy on AlGaIn/GaN metal-oxide semiconductor high electron mobility transistors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, 051208.	0.6	9
117	Effect of spacer layer thickness on structural and optical properties of multi-stack InAs/GaAsSb quantum dots. Applied Physics Letters, 2015, 107, 173109.	1.5	8
118	Quasi-two-dimensional electron gas at the interface of $\hat{\Gamma}^3$ -Al ₂ O ₃ /SrTiO ₃ heterostructures grown by atomic layer deposition. Journal of Applied Physics, 2015, 118, .	1.1	30
119	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi ₂ Te ₃ by Multifunctionality of Native Defects. Advanced Materials, 2015, 27, 3681-3686.	11.1	97
120	An indirect method of studying band alignments in nBn photodetectors using off-axis electron holography. Applied Physics Letters, 2015, 107, .	1.5	6
121	Polymerase Chain Reaction on a Viral Nanoparticle. ACS Synthetic Biology, 2015, 4, 1316-1325.	1.9	5
122	Interface engineered wetting-layer-free InAs quantum dots on GaAs(001). , 2015, , .		0
123	Formation of metastable phases in magnesium-titanium system by high-pressure torsion and their hydrogen storage performance. Acta Materialia, 2015, 99, 150-156.	3.8	73
124	Measurement of mean inner potential and inelastic mean free path of ZnO nanowires and nanosheet. Materials Research Express, 2015, 2, 105003.	0.8	4
125	Atomic layer deposition of crystalline SrHfO ₃ directly on Ge (001) for high- <i>k</i> dielectric applications. Journal of Applied Physics, 2015, 117, .	1.1	43
126	Carrier density modulation in a germanium heterostructure by ferroelectric switching. Nature Communications, 2015, 6, 6067.	5.8	75

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127	Molecular beam epitaxy growth of antimony-based mid-infrared interband cascade photodetectors. Journal of Crystal Growth, 2015, 425, 364-368.	0.7	7
128	Defect creation in InGaAs/GaAs multiple quantum wells. Structural properties. Journal of Crystal Growth, 2015, 425, 43-48.	0.7	6
129	Molecular Dynamics Simulation Study of the Association of Lidocainium Docusate and Its Derivatives in Aqueous Solution. Molecular Pharmaceutics, 2015, 12, 1893-1901.	2.3	16
130	Domain structure and perpendicular magnetic anisotropy in CoFe/Pd multilayers using off-axis electron holography. Journal of Magnetism and Magnetic Materials, 2015, 388, 16-21.	1.0	6
131	MBE growth of sharp interfaces in dilute-nitride quantum wells with improved nitrogen-plasma design. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, 031209.	0.6	9
132	Î±-1-Antitrypsin variants and the proteinase/antiproteinase imbalance in chronic obstructive pulmonary disease. American Journal of Physiology - Lung Cellular and Molecular Physiology, 2015, 308, L179-L190.	1.3	49
133	Direct detection and measurement of wall shear stress using a filamentous bio-nanoparticle. Nano Research, 2015, 8, 3307-3315.	5.8	7
134	Quasi-two-dimensional electron gas at the epitaxial alumina/SrTiO ₃ interface: Control of oxygen vacancies. Journal of Applied Physics, 2015, 117, .	1.1	37
135	Recovery in dc and rf performance of off-state step-stressed AlGaIn/GaN high electron mobility transistors with thermal annealing. Applied Physics Letters, 2015, 106, .	1.5	4
136	Plastic Deformation of BaTiO ₃ Ceramics by High-pressure Torsion and Changes in Phase Transformations, Optical and Dielectric Properties. Materials Research Letters, 2015, 3, 216-221.	4.1	64
137	Investigation of MBE-grown InAs _{1-x} Bi alloys and Bi-mediated type-II superlattices by transmission electron microscopy. Journal of Crystal Growth, 2015, 425, 250-254.	0.7	20
138	Glyph-Based Video Visualization for Semen Analysis. IEEE Transactions on Visualization and Computer Graphics, 2015, 21, 980-993.	2.9	23
139	Investigation of single-layer/multilayer self-assembled InAs quantum dots on GaAs _{1-x} Sb _x /GaAs composite substrates. Journal of Applied Physics, 2015, 118, .	1.1	4
140	Effect of interfacial oxygen on the microstructure of MBE-grown homoepitaxial N-polar GaN. Journal of Crystal Growth, 2015, 409, 14-17.	0.7	14
141	Characterization of Nanomaterials Using Transmission Electron Microscopy. RSC Nanoscience and Nanotechnology, 2015, , 1-29.	0.2	31
142	Using structural disorder to enhance the magnetism and spin-polarization in Fe _x Si _{1-x} thin films for spintronics. Materials Research Express, 2014, 1, 026102.	0.8	11
143	Improving the Spatial Resolution of Atomic-Scale EDS Mapping for Chemical Imaging and Quantification of Metallic Alloy Structures. Microscopy and Microanalysis, 2014, 20, 130-131.	0.2	0
144	A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors. Advanced Materials Interfaces, 2014, 1, 1400081.	1.9	40

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145	Epitaxial growth: Phenomenological model of defect creation. , 2014, , .		1
146	Band alignment of a HfO ₂ -VO ₂ -HfO ₂ confined well structure on silicon. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 011203.	0.6	5
147	Epitaxy of polar semiconductor Co ₃ O ₄ (110): Growth, structure, and characterization. Journal of Applied Physics, 2014, 115, .	1.1	27
148	Atomic and electronic structure of the ferroelectric BaTiO ₃ /Ge(001) interface. Applied Physics Letters, 2014, 104, .	1.5	45
149	Microstructure of Ti/Al/Ni/Au ohmic contacts for N-polar GaN/AlGa _N high electron mobility transistor devices. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 011201.	0.6	5
150	Determination of Polarization Fields Across Polytype Interfaces in InAs Nanopillars. Advanced Materials, 2014, 26, 1052-1057.	11.1	27
151	Microscopic Investigation of Mono-layer/Multi-layer self-assembled InAs QDs on GaAs _{1-x} Sb _x /GaAs Composite Substrates for Photovoltaic Solar Cells. Microscopy and Microanalysis, 2014, 20, 554-555.	0.2	0
152	High quality MBE grown dilute nitride quantum wells with novel Nitrogen-plasma source design. , 2014, , .		1
153	Molecular beam epitaxy using bismuth as a constituent in InAs and a surfactant in InAs/InAsSb superlattices. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	0.6	25
154	Effect of proton irradiation on AlGa _N /Ga _N high electron mobility transistor off-state drain breakdown voltage. Applied Physics Letters, 2014, 104, .	1.5	21
155	Enhancement of AlGa _N /Ga _N high electron mobility transistors off-state drain breakdown voltage via backside proton irradiation. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 021203.	0.6	7
156	Structural and optical properties of multi-stack InAs/GaAsSb quantum dots with different Sb composition. , 2014, , .		0
157	InGaAs/GaAs MQWs: Correlation of crystal and physical properties. , 2014, , .		0
158	Characterization of a-plane Ga _N templates grown by HVPE and high efficiency deep UV emitting AlGa _N /Al _N MQWs grown by MBE on such templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 585-589.	0.8	3
159	Nanostructure Property Control in AlP ₃ /Si(100) Semiconductors Using Direct Molecular Assembly: Theory Meets Experiment at the Atomic Level. Chemistry of Materials, 2014, 26, 4092-4101.	3.2	6
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